# N-Channel 40-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed

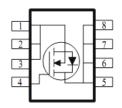
## **Typical Applications:**

- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY			
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
40	4.7 @ V <sub>GS</sub> = 10V	100 <sup>C</sup>	
40	6.9 @ V <sub>GS</sub> = 4.5V	90	

DFN5X6-8L





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			40	V		
Gate-Source Voltage			±20	V		
	T <sub>A</sub> =25°C		27			
Continuous Drain Current	T <sub>A</sub> =70°C	I <sub>D</sub>	22	A		
	T <sub>C</sub> =25°C		100 <sup>C</sup>			
	T <sub>C</sub> =70°C		87			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	135				
Continuous Source Current (Diode Conduction) <sup>a</sup>	۱ <sub>s</sub>	8.1				
	T <sub>A</sub> =25°C		5 <sup>a</sup>			
Power Dissipation	T <sub>A</sub> =70°C	P <sub>D</sub>	3.2 <sup>a</sup>	W		
	T <sub>C</sub> =25°C	۱D	83	vv		
	T <sub>c</sub> =70°C		53			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	25	°C/W			
	Steady State	INθJA	65				
Maximum Junction-to-Case (Drain)	Steady State	$R_{ extsf{ heta}JC}$	1.5				

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

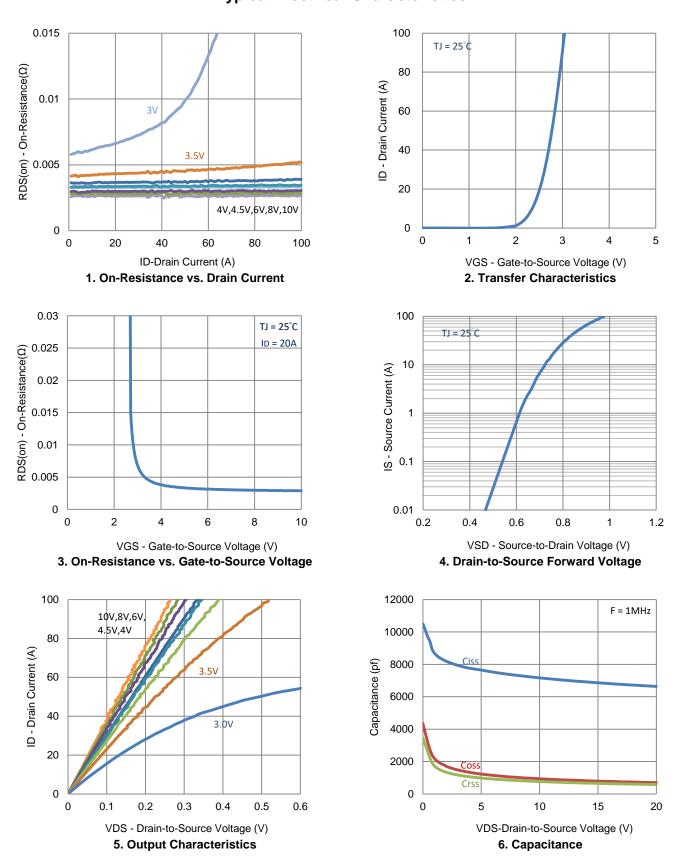
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 32 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	uA	
Zero Gale Voltage Drain Current	IDSS	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	40			А	
Drain Source On Registeres	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$			4.7		
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 16 \text{ A}$			6.9	mΩ	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		25		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 4.1 A, V <sub>GS</sub> = 0 V		0.69		V	
		Dynamic					
Total Gate Charge	Qg	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		49			
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS} = 20$ V, $V_{\rm GS} = 4.5$ V, $I_{\rm D} = 20$ A		12		nC	
Gate-Drain Charge	Q <sub>gd</sub>	1 <sub>D</sub> = 20 A		23			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 20 \text{ V}, \text{ R}_{L} = 1 \Omega,$		19			
Rise Time	t <sub>r</sub>	$v_{DS} = 20 \text{ v}, \text{ R}_{L} - 1 \Omega_{2},$ $I_{D} = 20 \text{ A},$		35		<b>n</b> 0	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		209		ns	
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = 10^{\circ} v$ , $v_{\text{GEN}} = 0.22^{\circ}$		88			
Input Capacitance	C <sub>iss</sub>			6861			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz		791		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			653			

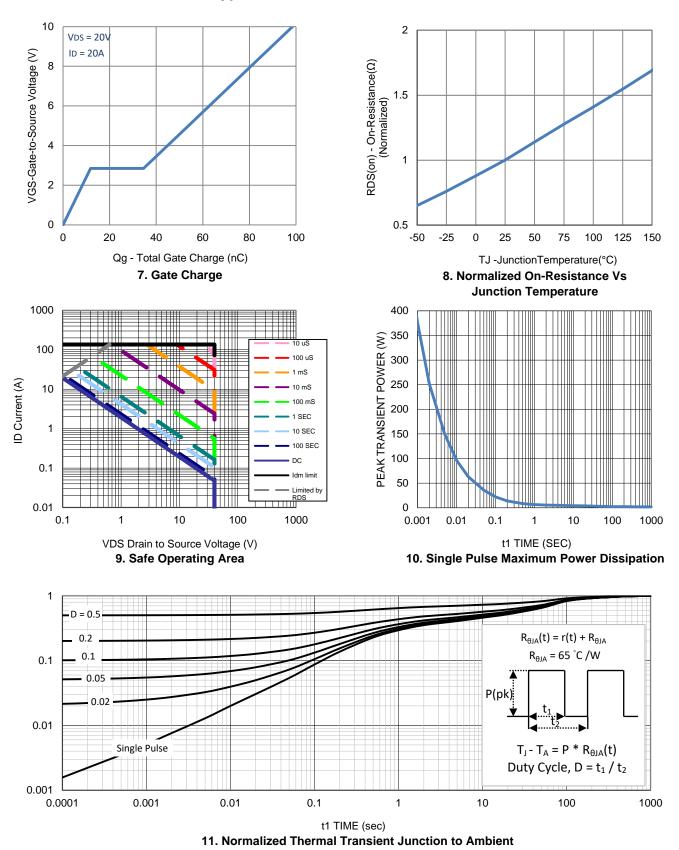
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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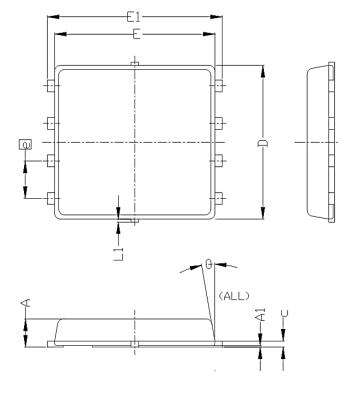
**Typical Electrical Characteristics** 

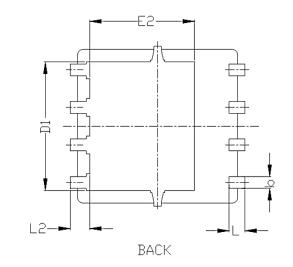


## **Typical Electrical Characteristics**

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# Package Information





SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMDULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D		5.20 BSC			0.205 BSC		
D1		4.35 BSC			0.171 BSC		
E		5.55 BSC		0.219 BSC			
E1	6.05 BSC			0.238 BSC			
E2	3.62 BSC			0.143 BSC			
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
Ll	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	